AN77Lxx/AN77LxxM Series

3-pin, positive output, low dropout voltage regulator (100 mA type)

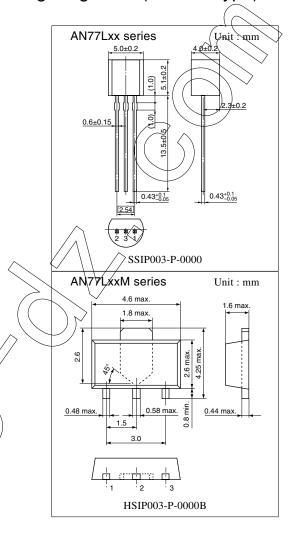
Overview

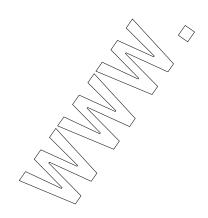
The AN77Lxx series and the AN77LxxM series are stabilized constant voltage power supplies with a low input/output voltage difference (0.22V typ. for AN77L03). It is suitable for the low-voltage equipment using batteries and consumer/industrial equipment with great fluctuation of the supply voltage.

■ Features

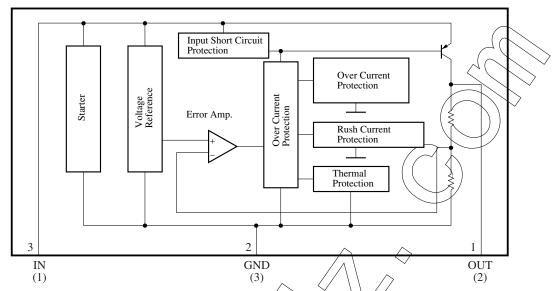
- Minimum input/output voltage difference:
 0.22V typ. (3V type)
- Built-in overcurrent limit circuit
- Built-in rush current prevention circuit at input voltage rise
- Built-in overheat protection circuit
- Built-in input short-circuit protection circuit

• Output voltage: 3V, 3.5V, 4V, 4.5V, 5V, 6V, 7V, 8V, 9V, 10V, 12V





■ Block Diagram (AN77LxxM series)



Note) The number in () shows the pin number for the AN77Lxx series.

■ Absolute Maximum Ratings at $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit
Supply voltage	V _{IN}	30	V
Supply current	I _{IN}	200	mA
Power dissipation *	PD	650	mW
Operating ambient temperature	Topr	-30 to +85	°C
Storage temperature	Tstg	−55 to +150	°C

^{*} HSIP003-P-0000B is mounted on a standard board (glass epoxy: 20mm × 20mm × 11.7mm with Cu foil of 1cm² or more).

■ Recommended Operating Range at Ta ≥ 25°C

Part No.	Output voltage (Vo)	Operation supply voltage range (V _I)	Unit
AN77L03, AN77L03M	3	V ₀ +0.3 to 13.62	V
AN77L035, AN77L035M	3.5	V_0 +0.41 to 14.14	V
AN77L04, AN77L04M	4	$V_0 + 0.3$ to 14.66	V
AN77L045, AN77L045M	4.5	V_0 +0.43 to 15.18	V
AN77L05, AN77L05M	5	$V_0 + 0.3$ to 15.7	V
AN77L06, AN77L06M	6	$V_{\rm O}$ +0.46 to 16.74	V
AN77L07, AN77L07M	7	$V_{\rm O}$ +0.48 to 17.78	V
AN77L08, AN77L08M	8	V_0 +0.51 to 18.82	V
AN77L09, AN77L09M	9	V ₀ +0.53 to 19.86	V
AN77L10, AN77L10M	10	V ₀ +0.55 to 20.9	V
AN77C12, AN77L12M	12	$V_0 + 0.6$ to 22.98	V

■ Electrical Characteristics at T_a = 25°C

• AN77L03, AN77L03M (3V, 100mA type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V_{O}	$T_j = 25^{\circ}C$	2.88	3	3.12	V
Line regulation	REG_{IN}	$V_I = 3.62 \text{ to } 13.62 \text{V}, T_j = 25^{\circ}\text{C}$	_	2	60	mV
Load regulation	REG_L	$I_0 = 0$ to 100mA, $T_j = 25^{\circ}C$		8	J (60)	mV
Bias current under no load	I_{Bias}	$I_0 = 0 \text{mA}, T_j = 25^{\circ}\text{C}$	_	0.9	1.5	mA
Bias current fluctuation to load	ΔI_{Bias}	$I_0 = 0$ to 100mA, $T_j = 25$ °C	_	(3)	5	mA
Bias current before regulation start	I_{rush}	$V_I = 2.7V$, $I_O = 0$ mA, $T_j = 25$ °C	_	(1(5	5	mA
Ripple rejection ratio	RR	$V_I = 3.62 \text{ to } 5.62 \text{V}, f = 120 \text{Hz}$	60	70		dB
Minimum input/output voltage difference 1	$V_{\text{DIF}(\text{min})1}$	$V_I = 2.7V$, $I_O = 50mA$, $T_j = 25$ °C	-	70.12	0.25	V
Minimum input/output voltage difference 2	$V_{\text{DIF}(\text{min})2}$	$V_I = 2.7V$, $I_O = 100mA$, $T_j = 25$ °C		0.32	0.3	V
Output noise voltage	V_{no}	f = 10Hz to 100 kHz	+/	70/		μV
Output voltage temperature coefficient	$\Delta V_{O}/T_{a}$	$T_j = -30 \text{ to } +125^{\circ}\text{C}$		0.2		mV/°C

Note 1) The specified condition $T_j = 25^{\circ}C$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_{\rm I}$ = 4V, $I_{\rm O}$ = 50mA and $C_{\rm O}$ = 10 μF

• AN77L035, AN77L035M (3.5V, 100mA type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	3.36	3.5	3.64	V
Line regulation	REG_{IN}	$V_1 = 4.14 \text{ to } 14.14 \text{V}, T_j = 25^{\circ}\text{C}$	_	3	60	mV
Load regulation	REG_L	$I_0 = 0$ to 100mA, $T_j = 25$ °C	_	9	60	mV
Bias current under no load	I_{Bias}	$I_0 = 0$ m A ; $T_j = 25$ °C		0.9	1.5	mA
Bias current fluctuation to load	ΔI_{Bias}	$I_0 = 0 \text{ to } 100 \text{mA}, T_j = 25^{\circ}\text{C}$	_	3	5	mA
Bias current before regulation start	I_{rush}	$V_1 \neq 3.15V$, $I_0 = 0mA$, $T_j = 25^{\circ}C$	_	1.5	5	mA
Ripple rejection ratio	RR	$\sqrt{1} = 4.14 \text{ to } 6.14 \text{V}, \text{ f} = 120 \text{Hz}$	59	69		dB
Minimum input/output voltage difference 1	V _{DIF(min)}	$V_1 = 3.15 \text{V}, I_0 = 50 \text{mA}, T_j = 25 ^{\circ}\text{C}$	_	0.12	0.25	V
Minimum input/output voltage difference 2	V _{DIF(min)2}	$V_1 = 3.15V$, $I_0 = 100mA$, $T_j = 25$ °C		0.22	0.41	V
Output noise voltage	V _{no}	f = 10 Hz to 100 kHz		75		μV
Output voltage temperature coefficient	$\Delta V_{O} T_{a}$	$T_j = -30 \text{ to } +125^{\circ}\text{C}$		0.23		mV/°C

Note 1) The specified condition $T_j = 25^{\circ}C$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = 4.5V$, $I_O = 50 \text{mA}$ and $C_O = 10 \mu\text{F}$

AN77L04, AN77L04M (4V, 100mA type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	\rangle v_{o}	$T_j = 25^{\circ}C$	3.84	4	4.16	V
Line regulation	REG _{IN}	$V_I = 4.66 \text{ to } 14.66 \text{V}, T_j = 25^{\circ}\text{C}$	_	3	60	mV
Load regulation	REG_L	$I_0 = 0$ to 100mA, $T_j = 25$ °C	_	9	60	mV
Bias current under no load	I_{Bias}	$I_0 = 0 \text{mA}, T_j = 25^{\circ}\text{C}$	_	0.9	1.5	mA
Bias current fluctuation to load	ΔI_{Bias}	$I_0 = 0$ to 100mA, $T_j = 25^{\circ}C$	_	3	5	mA
Bias current before regulation start	I_{rush}	$V_I = 3.6V, I_O = 0mA, T_j = 25^{\circ}C$	_	1.5	5	mA
Ripple rejection ratio	RR	$V_I = 4.66$ to 6.66V, $f = 120$ Hz	59	69		dB
Minimum input/output voltage difference 1	$V_{\text{DIF}(min)1}$	$V_I = 3.6V, I_O = 50mA, T_j = 25^{\circ}C$	_	0.12	0.25	V
Minimum input/output voltage difference 2	$V_{\text{DIF}(\text{min})2}$	$V_I = 3.6V, I_O = 100mA, T_j = 25^{\circ}C$		0.23	0.3	V
Output noise voltage	V_{no}	f = 10Hz to $100kHz$		80		μV
Output voltage temperature coefficient	$\Delta V_{O}/T_{a}$	$T_j = -30 \text{ to } +125^{\circ}\text{C}$		0.26		mV/°C

Note 1) The specified condition $T_j = 25^{\circ}C$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = 5V$, $I_O = 50$ mA and $C_O = 10\mu$ F

■ Electrical Characteristics at T_a = 25°C (continued)

• AN77L045, AN77L045M (4.5V, 100mA type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	4.32	4.5	4.68	V
Line regulation	REG _{IN}	$V_I = 5.18 \text{ to } 15.18 \text{V}, T_j = 25^{\circ}\text{C}$	_	3	60	mV
Load regulation	REG_L	$I_0 = 0$ to 100mA, $T_j = 25$ °C		10	J (60)	mV
Bias current under no load	I_{Bias}	$I_0 = 0 \text{mA}, T_j = 25^{\circ}\text{C}$	_	0.9	1.5	mA
Bias current fluctuation to load	ΔI_{Bias}	$I_0 = 0$ to 100mA, $T_j = 25$ °C		3	5	→ mA
Bias current before regulation start	I_{rush}	$V_I = 4.05V, I_O = 0mA, T_j = 25^{\circ}C$		(1.5	5	mA
Ripple rejection ratio	RR	$V_I = 7.18$ to 6.18V, $f = 120$ Hz	58	68	4	dB
Minimum input/output voltage difference 1	$V_{\text{DIF}(\text{min})1}$	$V_I = 4.05V, I_O = 50mA, T_j = 25^{\circ}C$	-/	70.12	0.25	V
Minimum input/output voltage difference 2	$V_{\text{DIF}(\text{min})2}$	$V_I = 4.05V, I_O = 100mA, T_j = 25$ °C	+(0.23	0.43	V
Output noise voltage	V_{no}	f = 10Hz to $100kHz$	+/	85/		μV
Output voltage temperature coefficient	$\Delta V_{O}/T_{a}$	$T_j = -30 \text{ to } +125^{\circ}\text{C}$		0.3		mV/°C

Note 1) The specified condition $T_j = 25^{\circ}$ C means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = 5.5V$, $I_O = 50 mA$ and $C_O = 10 \mu F$

• AN77L05, AN77L05M (5V, 100mA type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V_{0}	$T_j = 25^{\circ}C$	4.8	5	5.2	V
Line regulation	REG_{IN}	$V_1 = 5.7 \text{ to } 15.7 \text{ V}, T_3 = 25^{\circ}\text{C}$		4	60	mV
Load regulation	REG_L	$I_0 = 0$ to 100mA, $T_j = 25$ °C		10	60	mV
Bias current under no load	I_{Bias}	$I_0 = 0$ m A ; $T_j = 25$ °C		0.9	1.5	mA
Bias current fluctuation to load	ΔI_{Bias}	$I_0 = 0 \text{ to } 100 \text{mA}, T_j = 25^{\circ}\text{C}$		3	5	mA
Bias current before regulation start	I_{rush}	$V_1 \neq 4.5V$, $I_0 = 0mA$, $T_j = 25^{\circ}C$		1.5	5	mA
Ripple rejection ratio	RR	$\sqrt{1} \le 5.7 \text{ to } 7.7 \text{V, } f = 120 \text{Hz}$	58	68		dB
Minimum input/output voltage difference 1	V _{DIF(min)}	$V_I = 4.5V$, $I_O = 50$ mA, $T_j = 25$ °C		0.12	0.25	V
Minimum input/output voltage difference 2	V _{DIF(min)2}	$V_I = 4.5$ V, $I_O = 100$ mA, $T_j = 25$ °C		0.24	0.3	V
Output noise voltage	V _{no}	f = 10 Hz to 100 kHz		90		μV
Output voltage temperature coefficient	$\Delta V_{O} T_{a}$	$T_j = -30 \text{ to } +125^{\circ}\text{C}$		0.33		mV/°C

Note 1) The specified condition $T_j = 25^{\circ}C$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = 6V$, $I_O = 50 \text{mA}$ and $C_O = 10 \mu F$

AN77L06, AN77L06M (6V, 100mA type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	\rangle v_{o}	$T_j = 25^{\circ}C$	5.76	6	6.24	V
Line regulation	REG _{IN}	$V_I = 6.74 \text{ to } 16.74 \text{V}, T_j = 25^{\circ}\text{C}$		4	60	mV
Load regulation	REG_L	$I_0 = 0$ to 100mA, $T_j = 25^{\circ}C$		11	60	mV
Bias current under no load	I_{Bias}	$I_0 = 0 \text{mA}, T_j = 25^{\circ}\text{C}$	_	0.9	1.5	mA
Bias current fluctuation to load	ΔI_{Bias}	$I_0 = 0$ to 100mA, $T_j = 25^{\circ}C$	_	3	5	mA
Bias current before regulation start	I_{rush}	$V_I = 5.4V, I_O = 0mA, T_j = 25^{\circ}C$	_	1.5	5	mA
Ripple rejection ratio	RR	$V_I = 6.74 \text{ to } 8.74 \text{V}, f = 120 \text{Hz}$	56	66		dB
Minimum input/output voltage difference 1	$V_{\text{DIF}(\text{min})1}$	$V_I = 5.4V$, $I_O = 50mA$, $T_j = 25$ °C	_	0.12	0.25	V
Minimum input/output yoltage difference 2	$V_{\text{DIF}(\text{min})2}$	$V_I = 5.4V, I_O = 100mA, T_j = 25^{\circ}C$		0.25	0.46	V
Output noise voltage	V_{no}	f = 10Hz to 100 kHz		105		μV
Output voltage temperature coefficient	$\Delta V_O/T_a$	$T_j = -30 \text{ to } +125^{\circ}\text{C}$		0.4		mV/°C

Note 1) The specified condition $T_j = 25^{\circ}C$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = 7V$, $I_O = 50 \text{mA}$ and $C_O = 10 \mu\text{F}$

■ Electrical Characteristics at T_a = 25°C (continued)

AN77L07, AN77L07M (7V, 100mA type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V_{O}	$T_j = 25^{\circ}C$	6.72	7.0	7.28	V
Line regulation	REG_{IN}	$V_I = 7.78 \text{ to } 17.78 \text{ V}, T_j = 25^{\circ}\text{C}$		5	70(mV
Load regulation	REG_L	$I_0 = 0$ to 100mA, $T_j = 25^{\circ}C$		11	J (70\	mV
Bias current under no load	I_{Bias}	$I_0 = 0 \text{mA}, T_j = 25^{\circ}\text{C}$		1.1	1.6	mA
Bias current fluctuation to load	ΔI_{Bias}	$I_0 = 0$ to 100mA, $T_j = 25^{\circ}C$		(3)	5	mA
Bias current before regulation start	I_{rush}	$V_I = 6.3V$, $I_O = 0mA$, $T_j = 25^{\circ}C$		(1(5	5	mA
Ripple rejection ratio	RR	$V_I = 7.78 \text{ to } 9.78 \text{V}, f = 120 \text{Hz}$	55	65		dB
Minimum input/output voltage difference 1	$V_{\text{DIF}(\text{min})1}$	$V_I = 6.3V, I_O = 50mA, T_j = 25^{\circ}C$		70.12	0.25	V
Minimum input/output voltage difference 2	$V_{\text{DIF}(\text{min})2}$	$V_I = 6.3V, I_O = 100mA, T_j = 25^{\circ}C$		0.26	0.48	V
Output noise voltage	V_{no}	f = 10Hz to $100kHz$	+/	120/		μV
Output voltage temperature coefficient	$\Delta V_{O}/T_{a}$	$T_j = -30 \text{ to } +125^{\circ}\text{C}$		0.46		mV/°C

Note 1) The specified condition $T_j = 25^{\circ}$ C means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = 8V$, $I_O = 50 \text{mA}$ and $C_O = 10 \mu F$

• AN77L08, AN77L08M (8V, 100mA type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V_{O}	$T_j = 25^{\circ}C$	7.68	8	8.32	V
Line regulation	REG _{IN}	$V_1 = 8.82 \text{ to } 18.82 \text{ V}, T_j = 25^{\circ}\text{C}$	_	5	80	mV
Load regulation	REG_L	$I_0 = 0$ to 100mA, $T_j = 25$ C		12	80	mV
Bias current under no load	I_{Bias}	$I_0 = 0$ m A ; $T_j = 25$ °C		1.1	1.6	mA
Bias current fluctuation to load	ΔI_{Bias}	$I_0 = 0$ to 100 mA, $T_j = 25$ °C		3	5	mA
Bias current before regulation start	I_{rush}	$V_1 \neq 7.2V$, $I_0 = 0$ mA, $T_j = 25$ °C	_	1.5	5	mA
Ripple rejection ratio	RR	$\sqrt{1} \neq 8.82$ to 10.82V, f = 120Hz	53	63		dB
Minimum input/output voltage difference 1	V _{DIF(min)}	$V_1 = 7.2V$, $I_0 = 50$ mA, $T_j = 25$ °C	_	0.12	0.25	V
Minimum input/output voltage difference 2	V _{DIF(min)2}	$V_I = 7.2V$, $I_O = 100mA$, $T_j = 25^{\circ}C$		0.27	0.51	V
Output noise voltage	V _{no}	f=10Hz to 100kHz		135		μV
Output voltage temperature coefficient	$\Delta V_{O} T_{a}$	$T_j = -30 \text{ to } +125^{\circ}\text{C}$		0.53		mV/°C

Note 1) The specified condition $T_j = 25^{\circ}C$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = 9V$, $I_O = 50 \text{mA}$ and $C_O = 10 \mu\text{F}$

• AN77L09, AN77L09M (9V, 100mA type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	$ ightarrow V_{ m o}$	$T_j = 25^{\circ}C$	8.64	9	9.36	V
Line regulation	REG _{IN}	$V_I = 9.86 \text{ to } 19.86 \text{V}, T_j = 25^{\circ}\text{C}$	_	6	90	mV
Load regulation	REG_L	$I_0 = 0$ to 100mA, $T_j = 25^{\circ}C$	_	13	90	mV
Bias current under no load	I_{Bias}	$I_0 = 0 \text{mA}, T_j = 25^{\circ}\text{C}$	_	1.2	1.7	mA
Bias current fluctuation to load	ΔI_{Bias}	$I_0 = 0$ to 100mA, $T_j = 25$ °C	_	3	5	mA
Bias current before regulation start	I_{rush}	$V_I = 8.1 \text{V}, I_O = 0 \text{mA}, T_j = 25^{\circ}\text{C}$		1.5	5	mA
Ripple rejection ratio	RR	$V_I = 9.86 \text{ to } 11.86 \text{V}, f = 120 \text{Hz}$	52	62		dB
Minimum input/output voltage difference 1	$V_{\text{DIF}(\text{min})1}$	$V_I = 8.1V, I_O = 50mA, T_j = 25^{\circ}C$		0.13	0.25	V
Minimum input/output yoltage difference 2	$V_{\mathrm{DIF}(\mathrm{min})2}$	$V_I = 8.1V, I_O = 100mA, T_j = 25^{\circ}C$	_	0.28	0.53	V
Output noise voltage	V_{no}	f = 10Hz to $100kHz$		150		μV
Output voltage temperature coefficient	$\Delta V_{O}/T_{a}$	$T_j = -30 \text{ to } +125^{\circ}\text{C}$		0.6		mV/°C

Note 1) The specified condition $T_j = 25^{\circ}C$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified, $V_I = 10V$, $I_O = 50mA$ and $C_O = 10\mu F$

■ Electrical Characteristics at T_a = 25°C (continued)

• AN77L10, AN77L10M (10V, 100mA type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V_{O}	$T_j = 25^{\circ}C$	9.6	10	10,4	V
Line regulation	REG_{IN}	$V_I = 10.9 \text{ to } 20.9 \text{V}, T_j = 25^{\circ}\text{C}$	_	7	100	mV
Load regulation	REG_L	$I_0 = 0$ to 100mA, $T_j = 25$ °C	_	14	V (00)	mV
Bias current under no load	I_{Bias}	$I_0 = 0 \text{mA}, T_j = 25^{\circ}\text{C}$	_	1.2	1.7	mA
Bias current fluctuation to load	ΔI_{Bias}	$I_0 = 0$ to 100mA, $T_j = 25$ °C	_	(3)	5	mA
Bias current before regulation start	I_{rush}	$V_I = 9.0V, I_O = 0mA, T_j = 25^{\circ}C$	_	(1(5	5	mA
Ripple rejection ratio	RR	$V_I = 10.9 \text{ to } 12.9 \text{V}, f = 120 \text{Hz}$	50	60		dB
Minimum input/output voltage difference 1	$V_{\text{DIF}(\text{min})1}$	$V_I = 9.0V, I_O = 50mA, T_j = 25^{\circ}C$	-	70.13	0.25	V
Minimum input/output voltage difference 2	$V_{\text{DIF}(\text{min})2}$	$V_I = 9.0V, I_O = 100mA, T_j = 25^{\circ}C$	+(0.29	0.55	V
Output noise voltage	V_{no}	f = 10Hz to 100 kHz	+/	165/		μV
Output voltage temperature coefficient	$\Delta V_{O}/T_{a}$	$T_j = -30 \text{ to } +125^{\circ}\text{C}$		0.67		mV/°C

Note 1) The specified condition $T_j = 25^{\circ}$ C means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

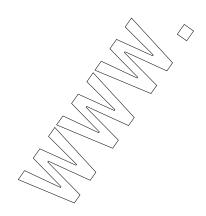
Note 2) Unless otherwise specified, $V_I = 11V$, $I_O = 50$ mA and $C_O = 10\mu$ F

• AN77L12, AN77L12M (12V, 100mA type)

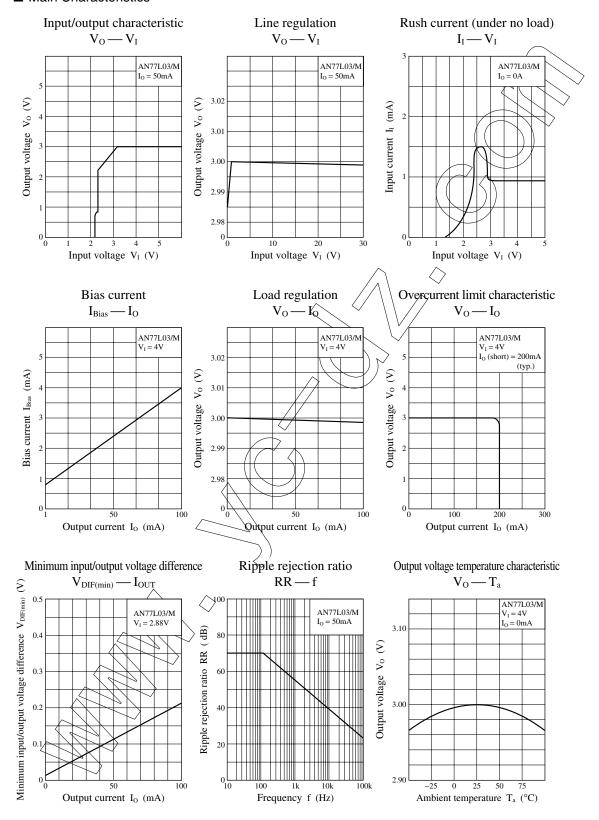
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	V_{O}	$T_j = 25^{\circ}C$	11.52	12	12.48	V
Line regulation	REG _{IN}	$V_I = 12.98 \text{ to } 22.98 \text{V}, T_J = 25^{\circ}\text{C}$		8	120	mV
Load regulation	REG_L	$I_0 = 0$ to 100mA, $T_j = 25$ °Cv		15	120	mV
Bias current under no load	I_{Bias}	$I_0 = 0$ m A ; $T_j = 25$ °C		1.4	1.9	mA
Bias current fluctuation to load	ΔI_{Bias}	$I_0 = 0 \text{ to } 100 \text{mA}, T_j = 25^{\circ}\text{C}$		3	5	mA
Bias current before regulation start	I_{rush}	$V_I \neq 10.8V$, $I_O = 0mA$, $T_j = 25$ °C		1.5	5	mA
Ripple rejection ratio	RR	$\sqrt{1} \le 12.98$ to 14.98V, f = 120Hz	48	58		dB
Minimum input/output voltage difference 1	V _{DIF(min)}	$V_I = 10.8V$, $I_O = 50mA$, $T_j = 25$ °C		0.13	0.25	V
Minimum input/output voltage difference 2	V _{DIF(min)2}	$V_I = 10.8V, I_O = 100mA, T_j = 25^{\circ}C$		0.31	0.6	V
Output noise voltage	V _{no}	f = 10 Hz to 100 kHz		190		μV
Output voltage temperature coefficient	$\Delta V_{O} T_{a}$	$T_j = -30 \text{ to } +125^{\circ}\text{C}$		0.8		mV/°C

Note 1) The specified condition $T_j = 25^{\circ}C$ means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

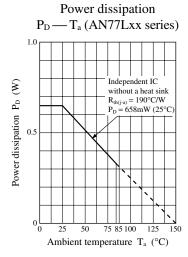
Note 2) Unless otherwise specified, $V_I = 13V$, $I_O = 50mA$ and $C_O = 10\mu F$



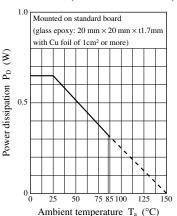
■ Main Characteristics

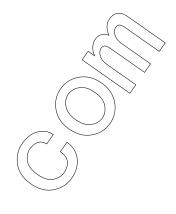


■ Main Characteristics (continued)



Power dissipation P_D — T_a (AN77LxxM series)





■ Usage Notes

1. Input short-circuit protection circuit

For the conventional Matsushita 3-pin regulators (such as of the AN80xx series), when DC input pin (pin 3) is short-circuited with GND pin (pin 2) in the normal operation condition, the potential of output pin (pin 1) becomes higher than that of DC input pin and the electric charges which is charged in output capacitor $C_{\rm O}$ flows in the input side, having resulted in the breakage of elements.

In the above case, the common silicon diode is connected as shown in the right figure (the dotted line). However, for the AN77Lxx/AN77LxxM series, since the protection circuit, which protects the elements from the discharging current, is incorporated in the internal circuit, the protection diode is not required.

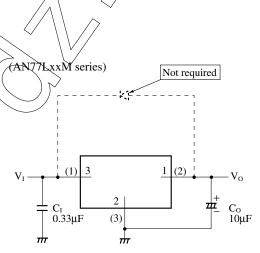
2. Short-circuit between the output pin and the GND pin

Because there is no in-built protection circuit in the AN77Lxx/ AN77LxxM series, they have the drooping characteristics as shown in the "Main Characteristics, Overcurrent limit characteristics". When your use under a high voltage happens to cause any short-circuit between the output pin (pin 1) and the GND pin (pin 2), the IC is likely to be broken.

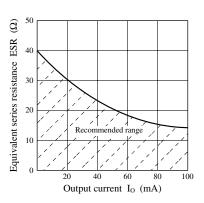
3. Capacitor for external compensation

In order to secure the stability, the capacitor of $10\mu F$ is required in the output side and it should be added as near to output pin (pin-1) and GND pin (pin 2) as possible. When it is used under low temperature, oscillation may occur due to the decrease of the aluminum electrolytic capacitor's capacitance and an increase of ESR.

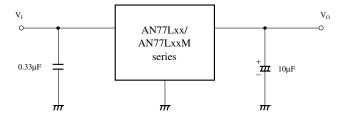
For the ANT/TLxx/AN77LxxM series, it is recommended that the tantalum capacitor or aluminum electrolytic capacitor whose equivalent serial resistance with temperature characteristics within the recommended range specified in the right figure should be used.



Note) The number in () shows the pin number for the AN77Lxx series.

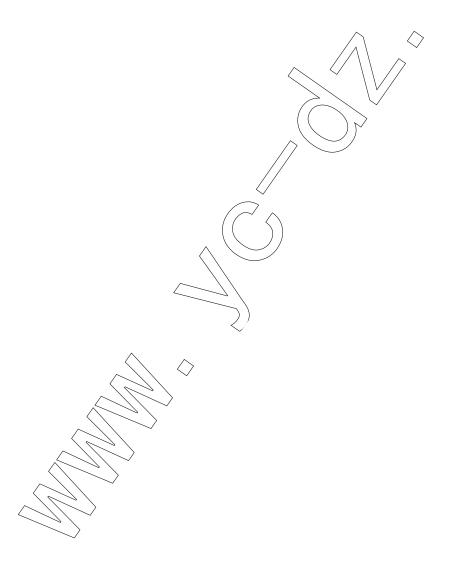


■ Application Circuit Example



• For the AN77Lxx/AN77LxxM series, the gain inside the IC is set high to improve the performance. For the reason, use the capacitor of 10µF or more when the power line in the output side is long.

In addition, install the capacitor in the output side as near as possible to the IC.



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